

# Wafer scale production of graphene: opportunities and challenges

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HVM Graphene Conference 5 November  
2013

[hvm-uk.com](http://hvm-uk.com)

# Who are we

- Applied Nanolayers BV
  - Company building a 200 mm CVD wafer production line for graphene in The Netherlands.



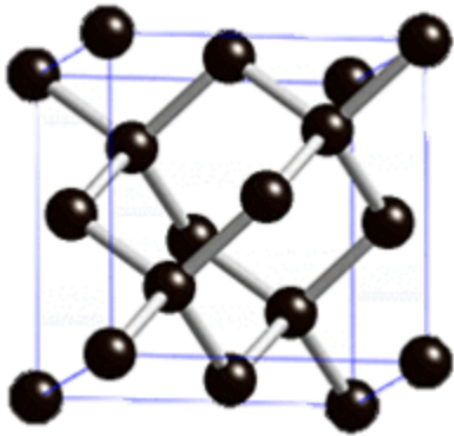
# Outline

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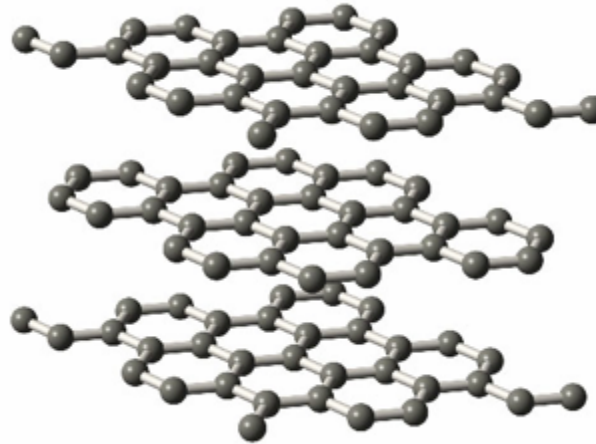
- ~~Graphene background and properties~~
- Production methods and challenges
- Transfer methods
- Quality control

# Carbon

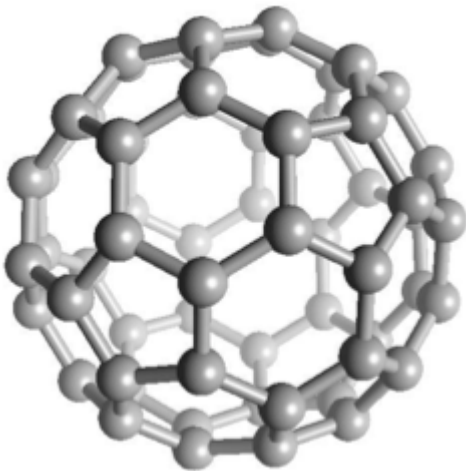
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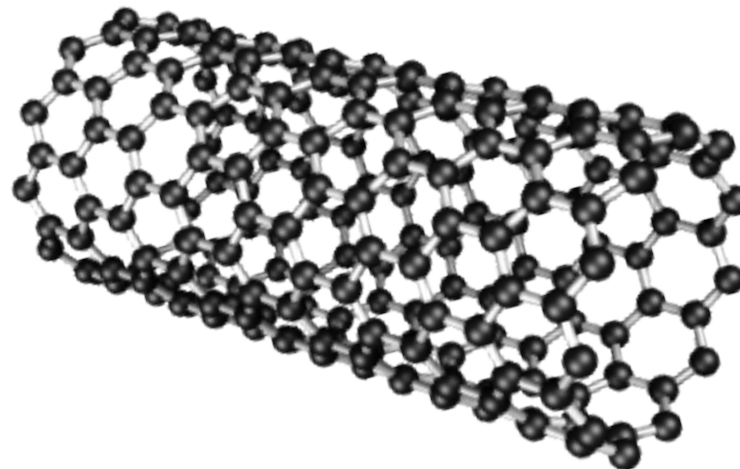
diamond



graphite



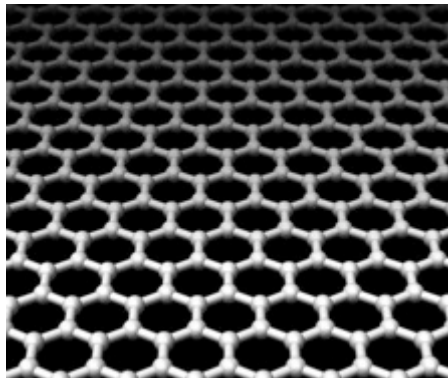
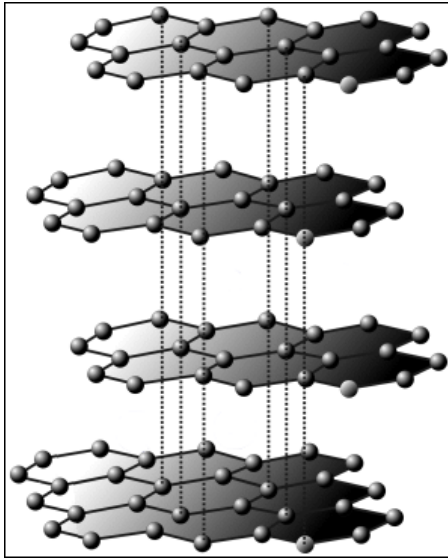
bucky balls



nanotubes

# Graphene

graphite



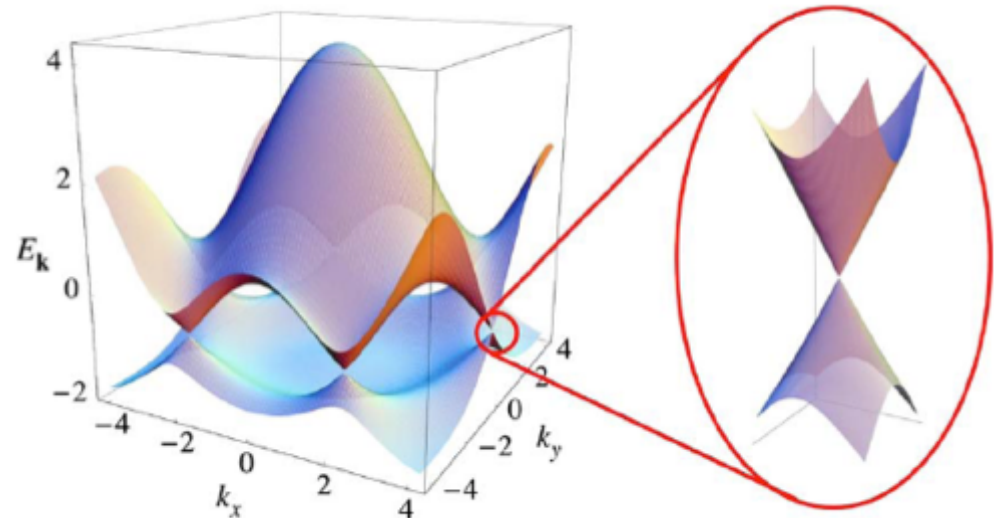
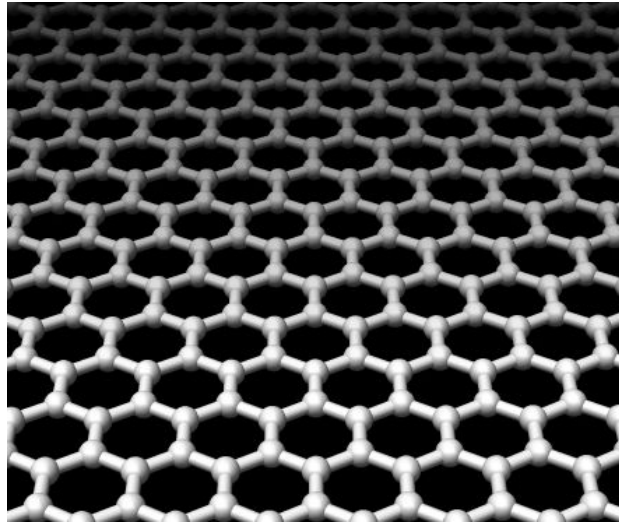
*Prof. Andre Geim*  
Nobel Prize  
Physics 2010



*'dream material':*

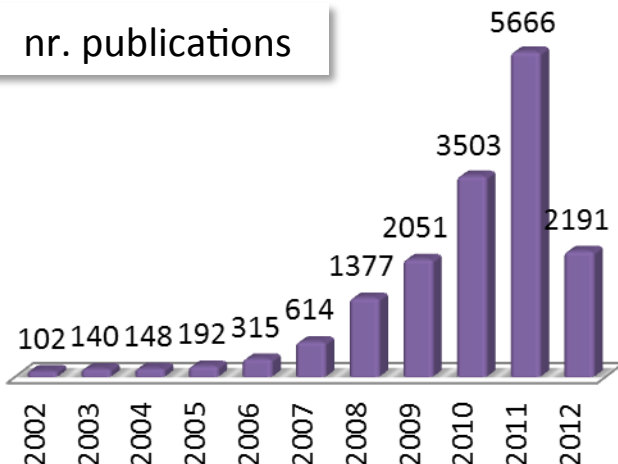
- Thinnest possible material!
  - first 'proposed' in 1947 (P.R. Wallace)
- Many special properties
  - first explored in 2004 (Geim et al.)

# Graphene trivia



Castro Neto, Guinea, Peres, Novoselov, Geim,  
*Rev.Mod.Phys.* **81**, 109 (2009)

nr. publications



- Electrons behave as 'massless Dirac fermions':  $E = \hbar v_F \sqrt{k_x^2 + k_y^2}$
- High electron (and hole) mobility
- Promising for future (flexible) electronics

# Properties

- Special properties and applications:

- High electron (hole) mobility

- 200,000 cm<sup>2</sup>V<sup>-1</sup>s<sup>-1</sup>: future chip technology addition to/(replacement of silicon?); 100 GHz transistor, 10 GHz mixer (IBM); low spin-orbit interaction (spintronics?)*

- Strong and flexible

- 1 TPa: (200 x steel): flexible electronics, MEMS resonators, sensors, membranes, coatings, enforcing material in composites, graphene 'paper'*

- High thermal conductivity

- 5000 Wm<sup>-1</sup>K<sup>-1</sup>: heat sink for electronic circuits*

- Optical properties

- graphene-based laser; 2.3% absorption of white light through single graphene layer; transparent conductor: replacement of indium-tin-oxide (touch screens)*

- Chemically inert

- protective coating: anti-corrosive, anti-adhesive, anti-friction/wear; impermeable*

- Efficient in charge storage

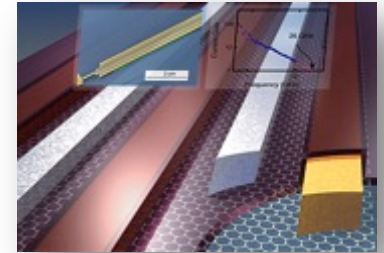
- 'ultra-capacitor': replacement of lithium batteries*

- Efficient in hydrogen storage

- energy storage medium*

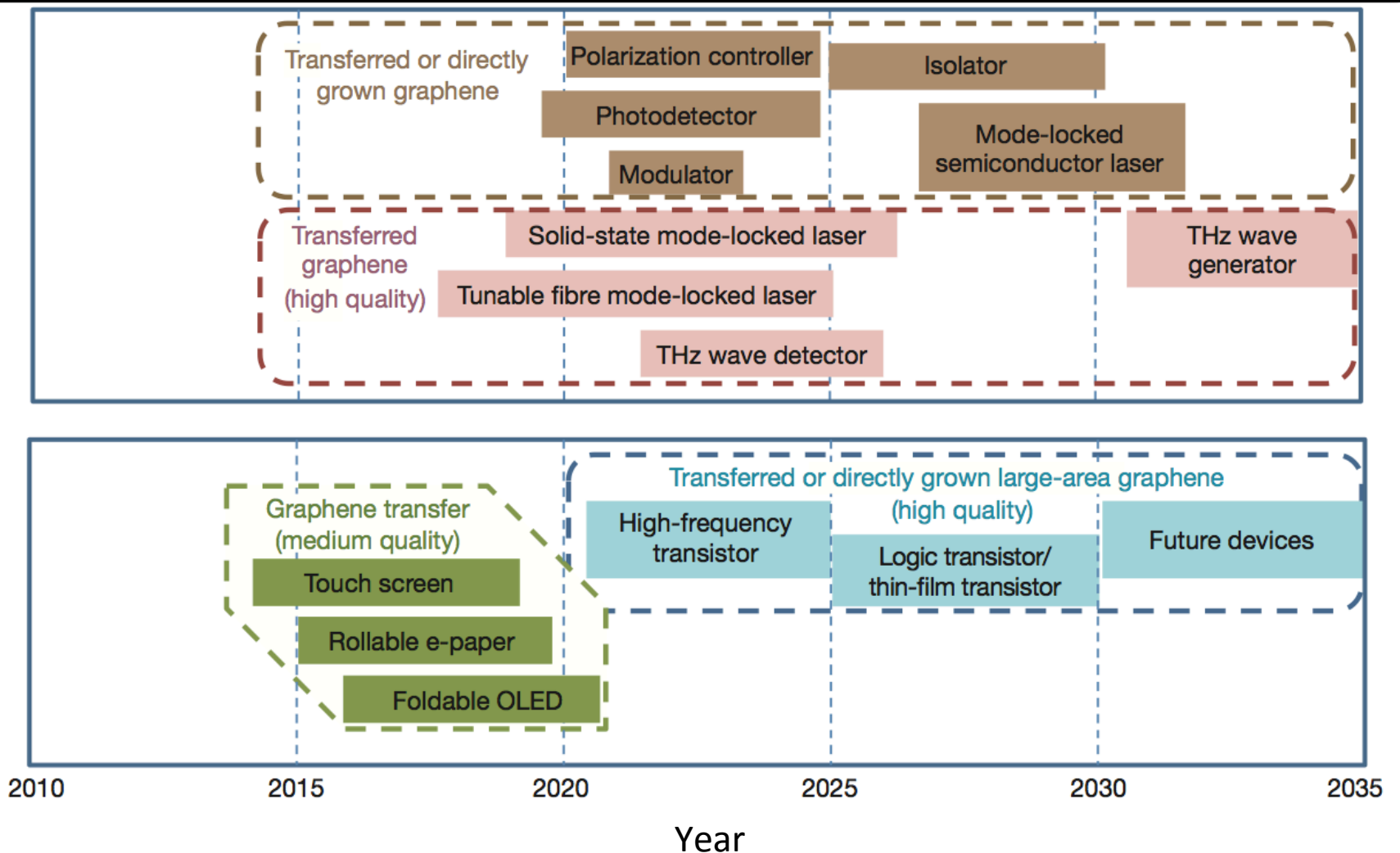
- Bio-compatible

- bio-sensors, bio-compatible coatings, anti-bacterial*





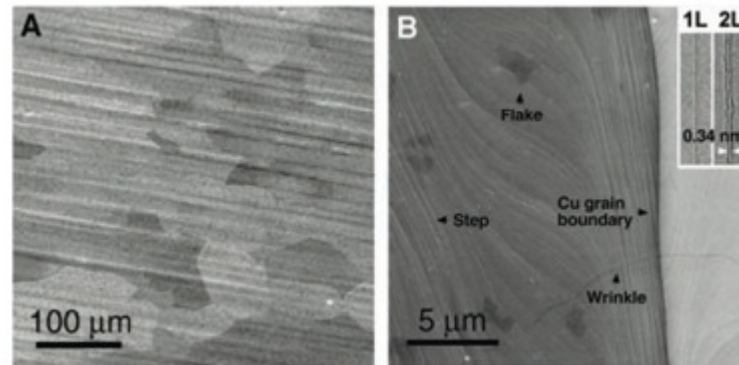
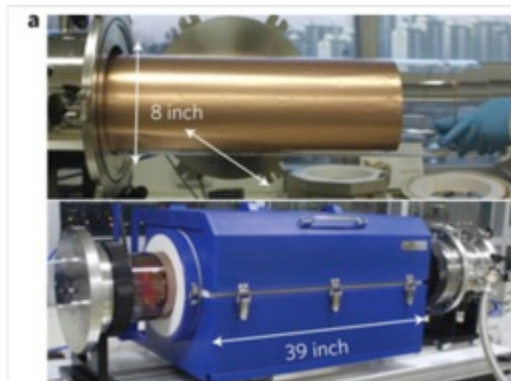
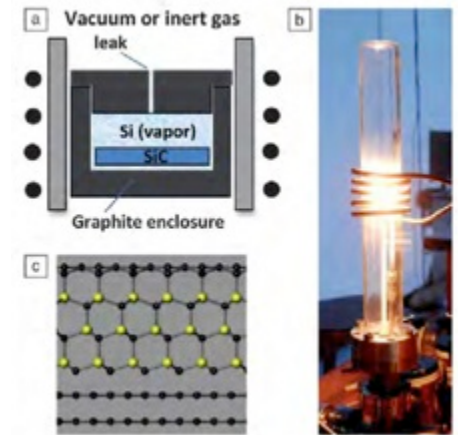
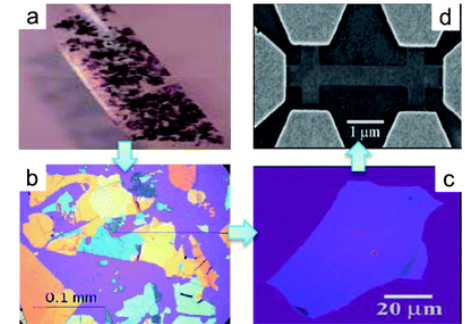
# Applications





# Production methods

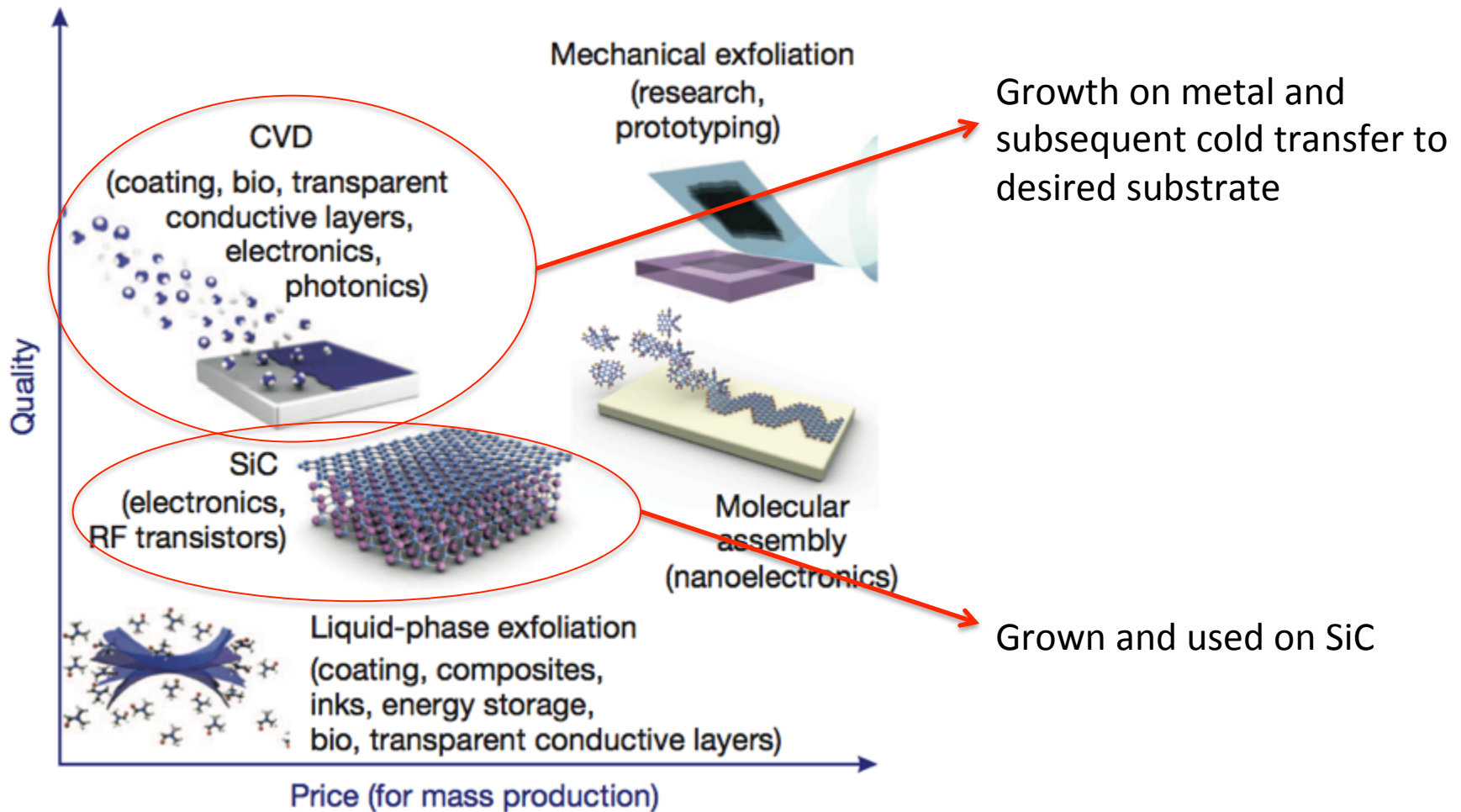
- Mechanical exfoliation
- Thermal decomposition of SiC
- CVD on transition metals



# Productions methods

Method	Crystallite size ( $\mu\text{m}$ )	Sample size (mm)	Mobility (ambient) ( $\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$ )	Applications
Mechanical exfoliation	> 1000	> 1	> $2 \cdot 10^5$	Research
Chemical exfoliation	$\leq 0.1$	Infinite as overlapping flakes	100	Coating, paint/ink, composites, transparent conductive layers, energy storage, bioapplications
Chemical exfoliation via graphene oxide	$\sim 100$	Infinite as overlapping flakes	1	Coating, paint/ink, composites, transparent conductive layers, energy storage, bioapplications
CVD	1000	$\sim 1000$	10000	Photonics, nanoelectronics, transparent conductive layers, sensors, bioapplications
SiC	50	100	10000	High frequency transistors and other electronic devices

# Production methods



Novoselov et al. *A roadmap for graphene*, Nature **490** (2012)

# CVD graphene

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- Growth on metals:
  - Single crystals
  - Foils
  - Epitaxial layers
- Metals:
  - Cu (cheap, low carbon solubility, SLG)
  - Ni (cheap, high carbon solubility, MLG)
  - Rh, Ru, Pt, Au, Ir, etc. (expensive)
- Methods
  - Thermal CVD
  - PE CVD
  - Carbon segregation

# Graphene as a platform

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- 2D materials used with graphene:
  - h-BN (insulator)
  - MoS<sub>2</sub> (semiconductor)
  - Many more...
- CVD production of h-BN layers is possible.
- h-BN and graphene can be grown or transferred on top of each other.
- Hybrid h-BN/graphene layers can also be synthesized.

# Live STM studies of graphene growth

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## High speed

- **Speed:** *video-STM*

*0.01 – 25 frames/s*

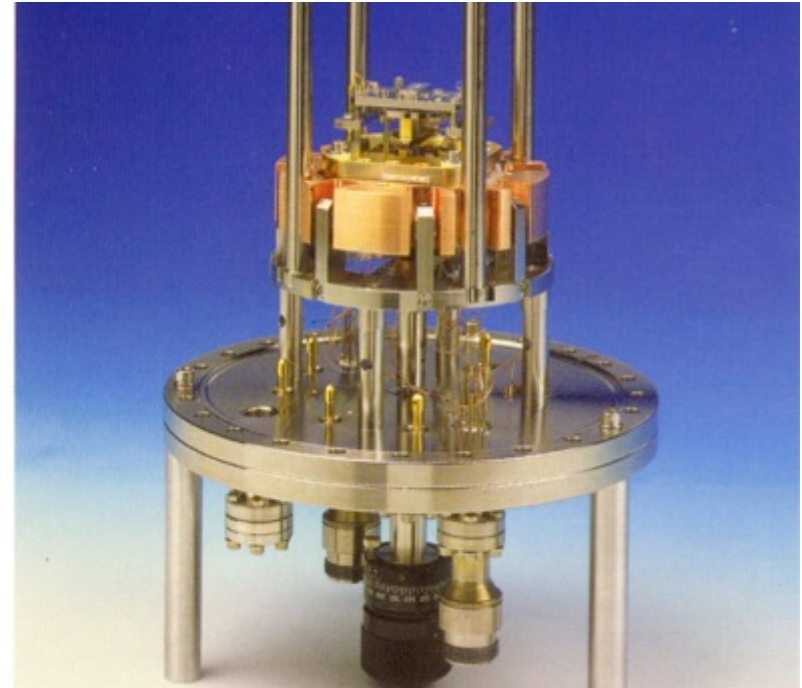
*(256x256 pixels) x2*

## Variable temperature

- **Range:** - *50 K – 1300 K*

- **Sweep:** - *full T-range:*  
*same area in sight' over 300 K*

- **'Secret':** - *finite-element analysis*



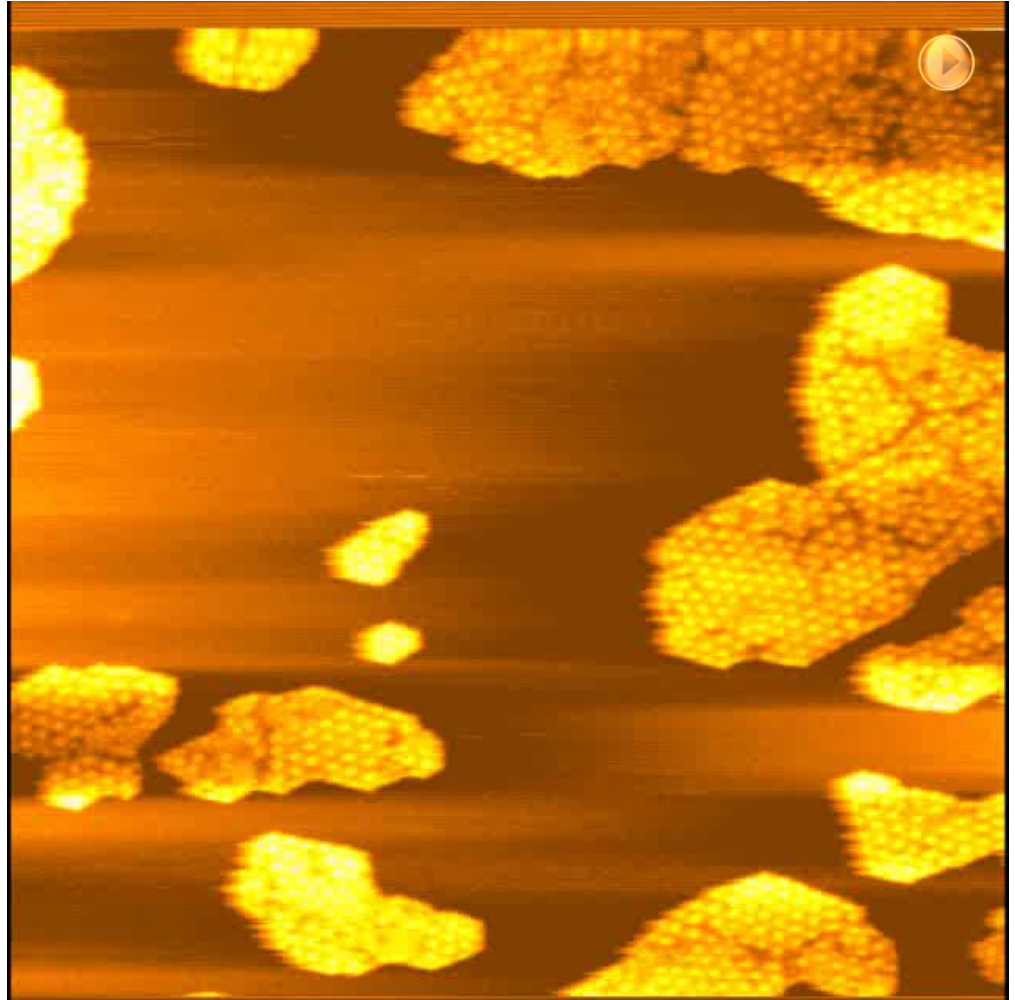
Hoogeman *et al.*, Rev.Sci.Instrum. **69** (1998) 2072

M.J. Rost *et al.*, Rev.Sci.Instrum. **76** (2005) 053710

# Graphene growth on rhodium

*Start:* Rh(111) seeded with graphene at RT by C<sub>2</sub>H<sub>4</sub>

*Movie:* further C<sub>2</sub>H<sub>4</sub> exposure at 975 K at 3X10<sup>-9</sup> ~1 X10<sup>-8</sup> mbar



Real time: 76mins

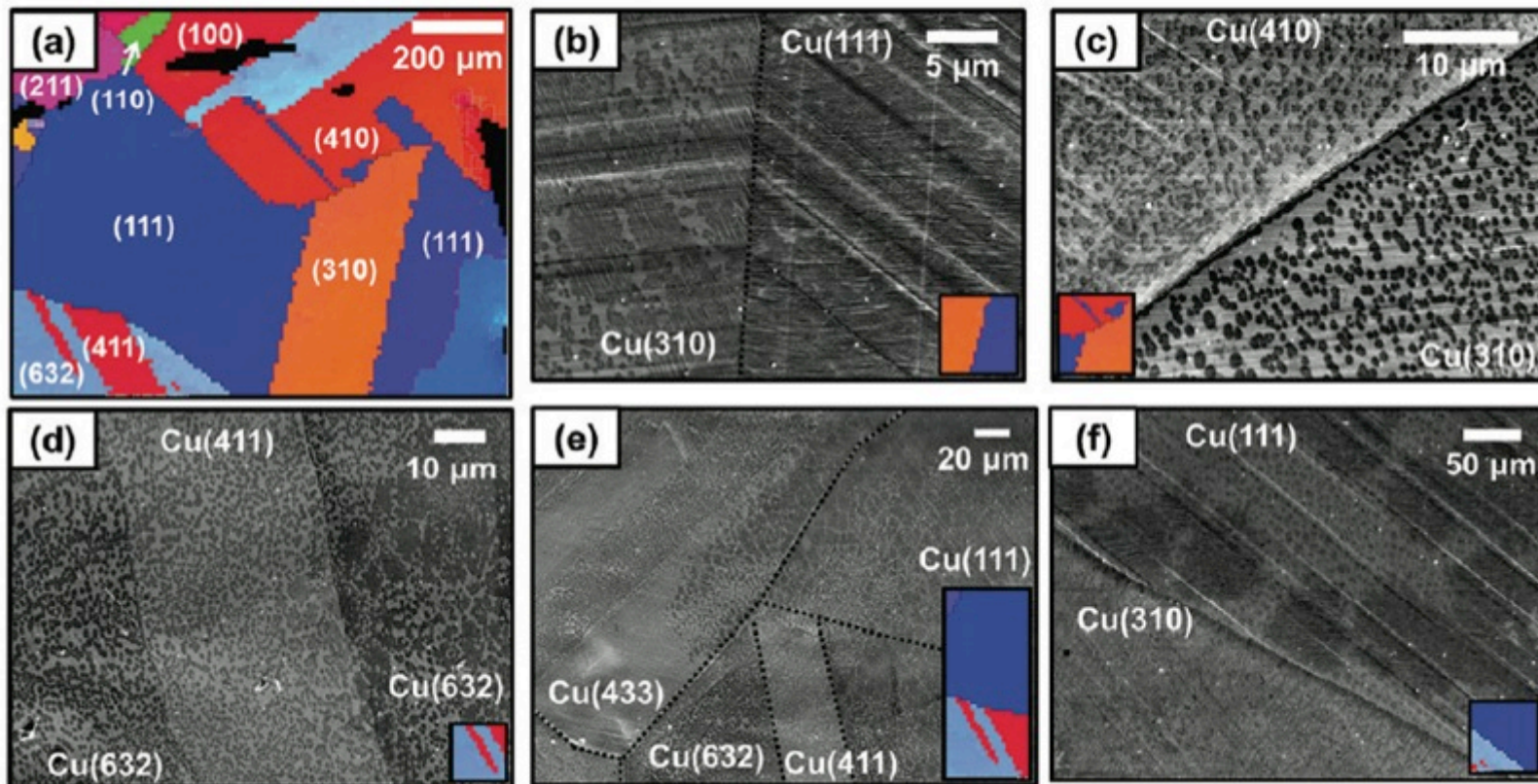
170 X 170nm<sup>2</sup>

I = 50 pA

V = -1.84 V

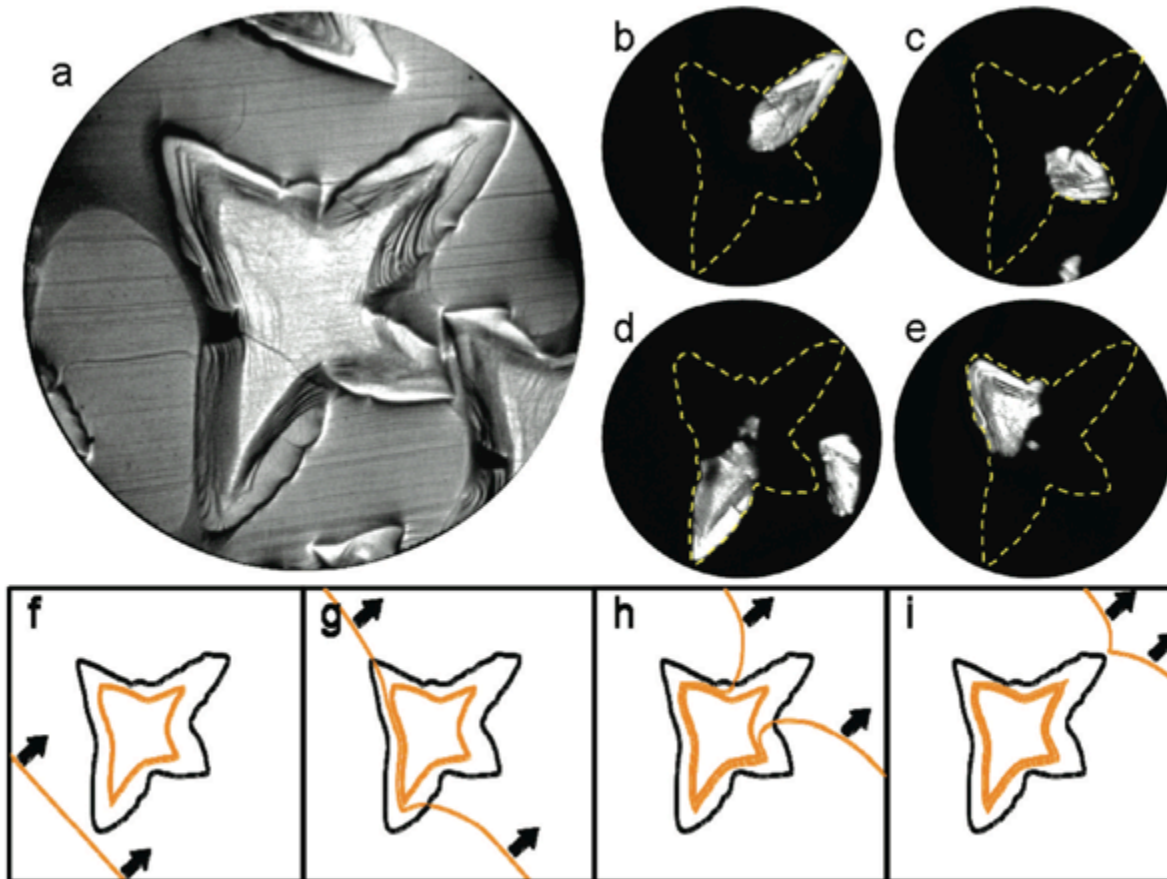


# Substrate orientation: or the problem with foil



Cu(111) gives highest quality graphene

# Crystalline Substrate Orientation



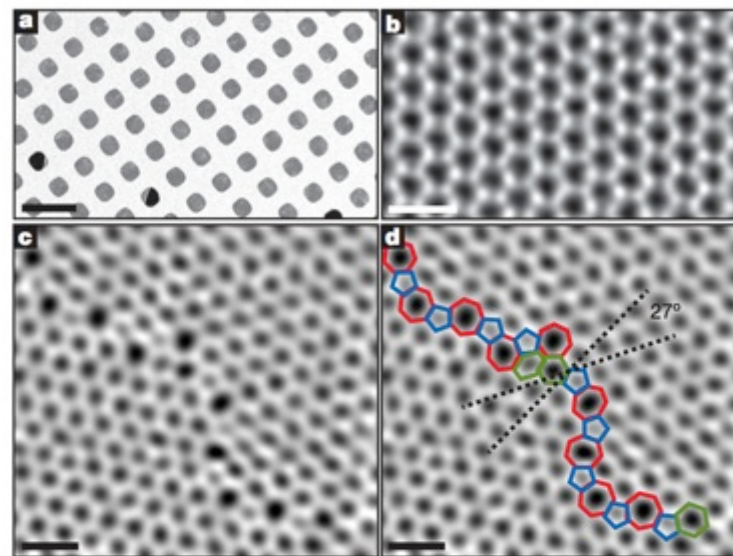
Cu(100) gives four different graphene domains in one graphene island

FIGURE 3. Bright (a) and dark field (b–e) LEEM images of a large graphene island on Cu(100) showing the spatial distribution of rotational variants. The graphene (01) direction is rotated by (b) 28°, (c) 2°, (d) 8°, and (e) 42°, relative to Cu(001) (FOV = 20  $\mu\text{m}$ , yellow dashes are the approximate island boundary). Cu step edge accumulation during growth results in a Cu hillock beneath the graphene island, as can be seen in (a). The hillock formation process is illustrated in (f–i).

# Grain boundary

## Grains and grain boundaries in single-layer graphene atomic patchwork quilts

Pinshane Y. Huang<sup>1\*</sup>, Carlos S. Ruiz-Vargas<sup>1\*</sup>, Arend M. van der Zande<sup>2\*</sup>, William S. Whitney<sup>2</sup>, Mark P. Levendorf<sup>3</sup>, Joshua W. Kevek<sup>4</sup>, Shivank Garg<sup>3</sup>, Jonathan S. Alden<sup>1</sup>, Caleb J. Hustedt<sup>5</sup>, Ye Zhu<sup>1</sup>, Jiwoong Park<sup>3,6</sup>, Paul L. McEuen<sup>2,6</sup> & David A. Muller<sup>1,6</sup>



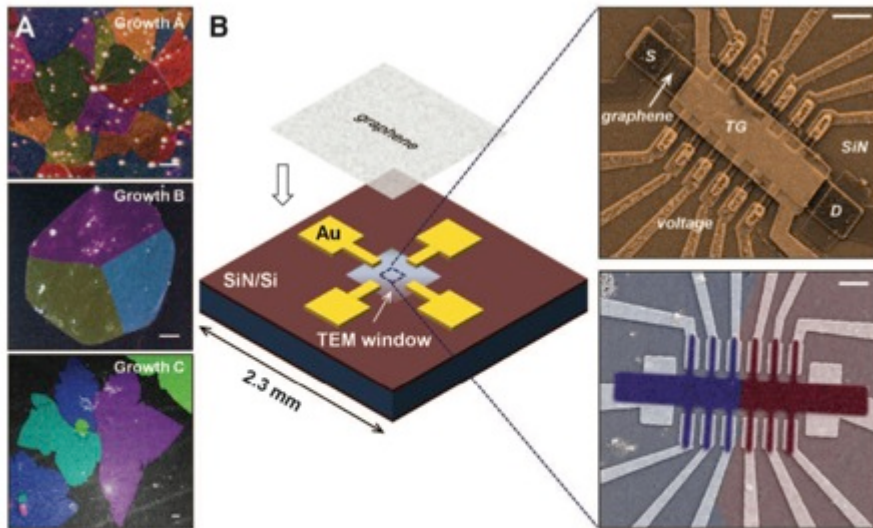
**Figure 1 | Atomic-resolution ADF-STEM images of graphene crystals.**  
**a**, Scanning electron microscope image of graphene transferred onto a TEM grid with over 90% coverage using novel, high-yield methods. Scale bar, 5  $\mu\text{m}$ .  
**b**, ADF-STEM image showing the defect-free hexagonal lattice inside a graphene grain. **c**, Two grains (bottom left, top right) intersect with a 27° relative rotation. An aperiodic line of defects stitches the two grains together. **d**, The image from **c** with the pentagons (blue), heptagons (red) and distorted hexagons (green) of the grain boundary outlined. **b–d** were low-pass-filtered to remove noise; scale bars, 5 Å.



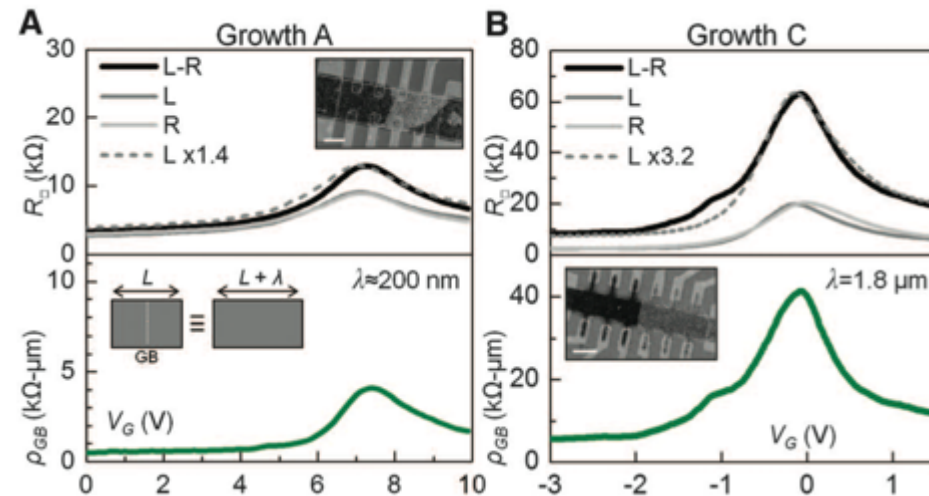
# Grain boundary

## Tailoring Electrical Transport Across Grain Boundaries in Polycrystalline Graphene

Adam W. Tsen,<sup>1</sup> Lola Brown,<sup>2</sup> Mark P. Levendorf,<sup>2</sup> Fereshte Ghahari,<sup>3</sup> Pinshane Y. Huang,<sup>1</sup> Robin W. Havener,<sup>1</sup> Carlos S. Ruiz-Vargas,<sup>1</sup> David A. Muller,<sup>1,4</sup> Philip Kim,<sup>3</sup> Jiwoong Park<sup>2,4\*</sup>



**Fig. 1.** (A) Composite false-color DF-TEM images of CVD graphene produced using three different growth conditions—A, B, and C—yielding average domain size  $D$  of 1, 10, and 50  $\mu\text{m}$ , respectively, in continuous films. (B) (Left) Schematic of specially fabricated TEM chip compatible with electron-beam lithography and electrical measurements. (Top right) SEM image of top-gated, graphene Hall bar device. (Bottom right) Overlaid SEM and DF-TEM images showing device crossing a single GB of two domains from growth C. Scale bars, 1  $\mu\text{m}$ .



Growth method determines grain boundary resistivity

# Graphene growth challenges

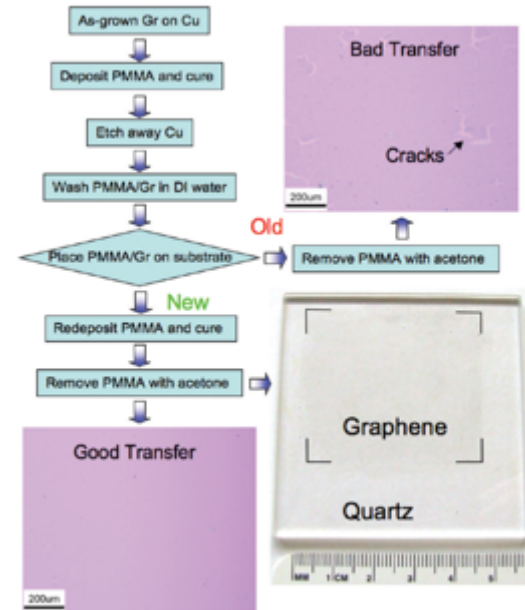
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- Control number of layers precisely
- Separate nucleation and growth
- Control domain size
- Control substrate/graphene morphology
- Control Chemical doping

# Transfer methods

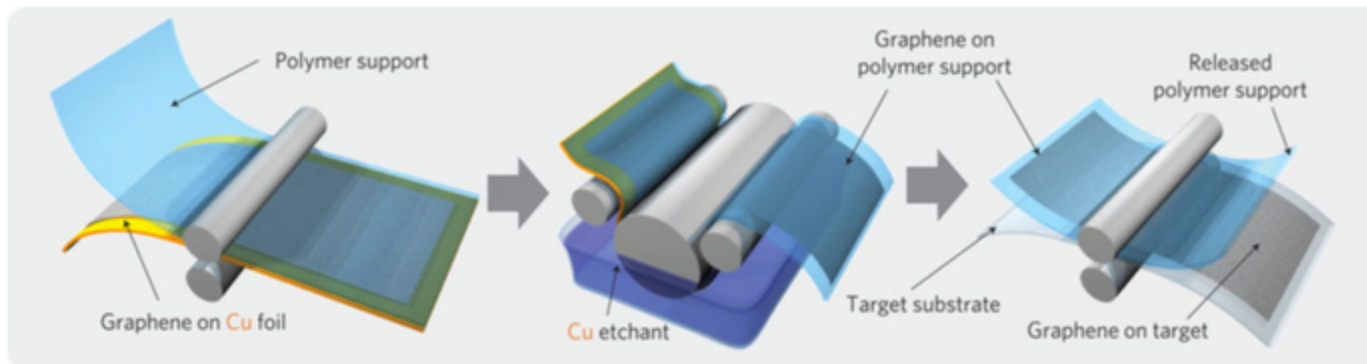
- PMMA assisted wet transfer

Li et al, Nano Letters 9 (2009)



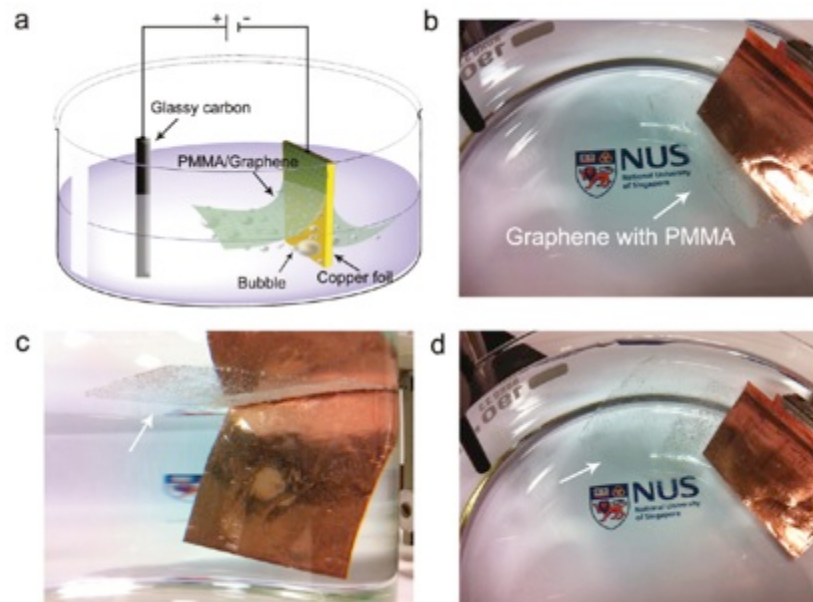
- Thermal release tape

Bae et al, Nature Nanotechnology 5 (2010)



# Transfer methods

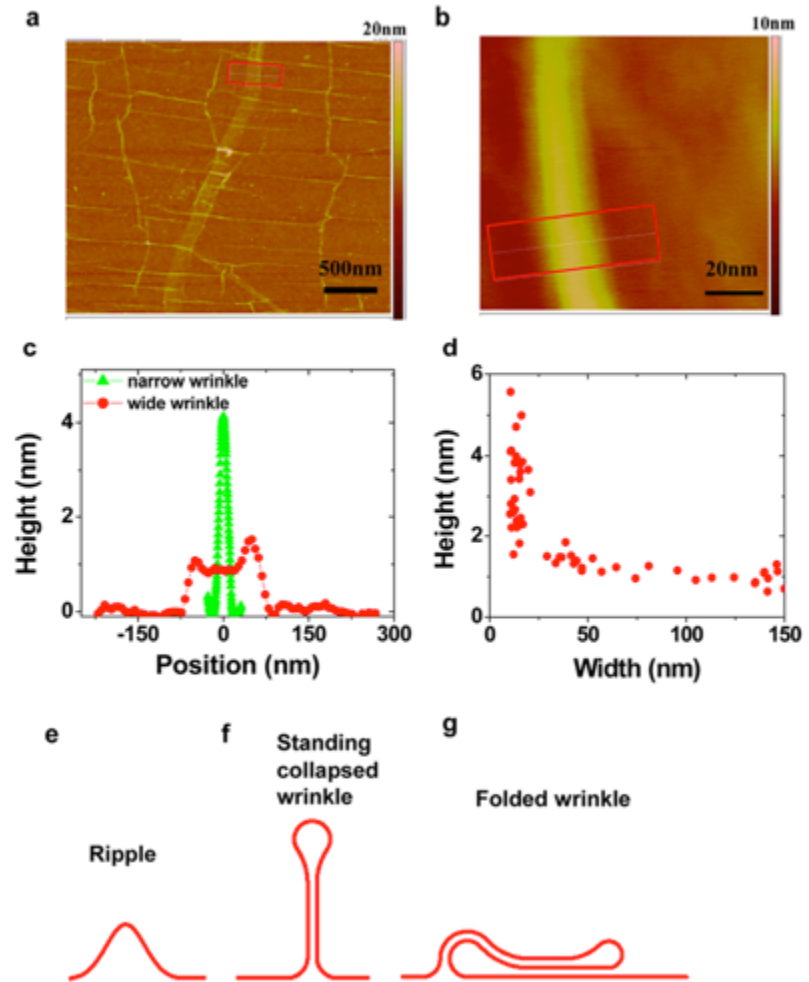
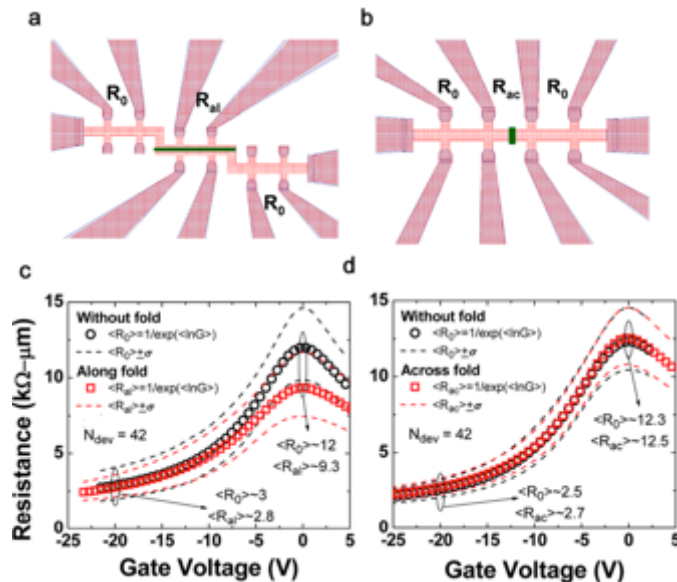
- Electrochemical delamination
  - No etching of (copper) substrate.  $H_2$  used to delaminate PMMA/G film
  - Substrate re-use possible with this method





# Transfer challenges

- Scalability/cost
- Chemical damage
- Mechanical damage
  - Holes, tears, wrinkles



Zhu et al , Nano Lett, **12** (2012)

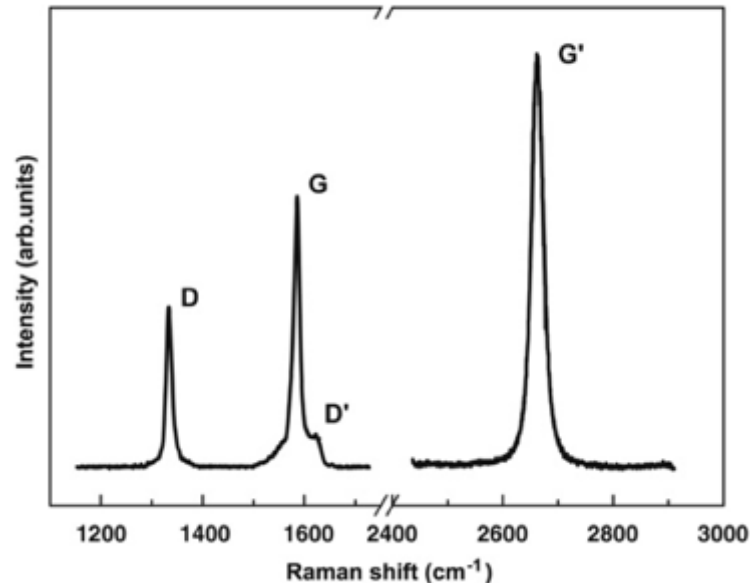
# Quality control

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- Graphene quality can relate to different properties:
  - Mobility, sheet resistance, grain size, roughness, defect density
  - Uniformity of different properties:
    - Doping
    - Layer number
    - Grain size
    - Structural defects
    - Morphology
  - Many more...
- ‘Low quality’ and ‘high quality’ are meaningless without a relation to the aspects of quality they refer to (and which aspects of quality are important for specific applications)

# Raman spectroscopy for quality control

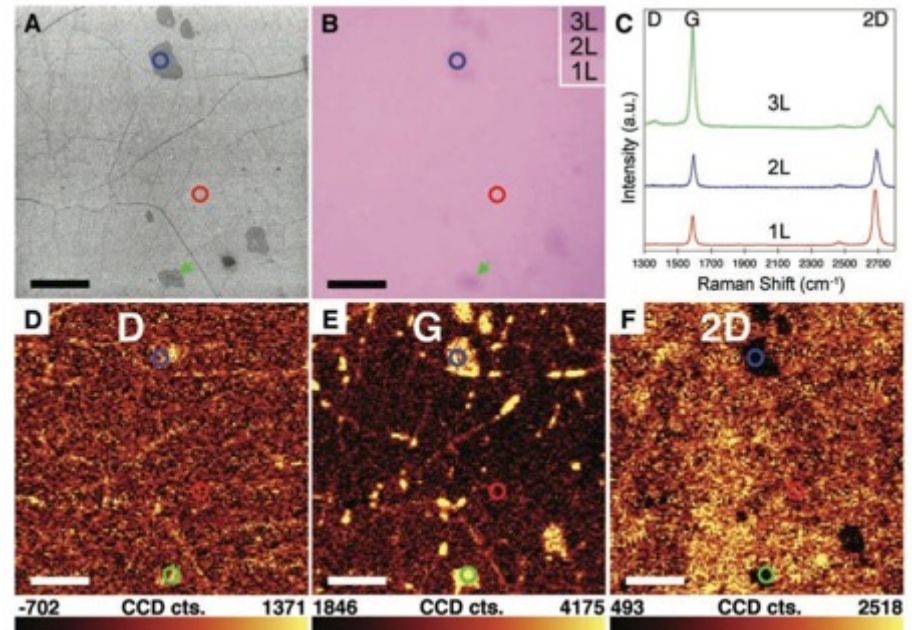
L.M. Malard et al. / Physics Reports 473 (2009) 51–87



Local properties taken from Raman spectrum relating to peak shapes, widths, heights and positions of the indicated peaks.

- Number of layers
- Presence of Raman active defects
- Average distance between defects
- Doping

## Mapping with micro-Raman



Li et al, Science **324** (2009)

# Barriers to industrialization

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- Quality control of material
- Integration into manufacturing
- Security of supply
- Material cost
- Short term application
- Control over / tuning of different properties

# Closing

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- Graphene comes in more than one form.
- Many ways of producing and transferring. These will be specific to certain applications.
- For graphene to be relevant a robust quality analysis chain through manufacturing must guarantee product is always the same!
- ANL is focused on building this chain and starting up a 200 mm production facility in the Netherlands.
- Contact details: [r.van.rijn@appliednanolayers.com](mailto:r.van.rijn@appliednanolayers.com)